

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO. 03500.017975.		APPLICATION NO. 10/549,900	
				APPLICANT SHUNICHI ISHIHARA			
				371(c) DATE September 20, 2005		GROUP 1753	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/X.T./		6,653,554	11/25/03	Ishihara	136	258	
/X.T./		6,387,780	05/14/02	Nishida	438	497	
/X.T./		5,246,886	09/21/93	Sakai, et al.	437	228	
/X.T./		2006/0194417	08/31/06	Ishihara, et al.	438	479	
/X.T./		2005/0136576	06/23/05	Ishihara, et al.	438	162	
/X.T./		2005/0066881	03/31/05	Nakagawa, et al.	117	18	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
/X.T./		2965094	08/13/99	Japan			Abstract
/X.T./		10-98205	04/14/98	Japan			Abstract
/X.T./		8-250433	09/27/96	Japan			Abstract
/X.T./		5-48128	02/26/93	Japan			Abstract
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
/X.T./		Haruo Itoh, et al., "Characterization of Silicon Layers Epitaxially Grown on Metallurgical-Grade Polycrystalline Substrates", Journal of Crystal Growth, Vol. 45, 1978, pp. 446-453.					
/X.T./		T. H. Wang, et al., "Growth of silicon thin layers on cast MG-Si from metal solutions for solar cells", Solar Energy Materials and Solar Cells, Vol. 41/42, 1996, pp. 19-30.					
EXAMINER				DATE CONSIDERED			
/Xiuyu Tai/				03/13/2008			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.